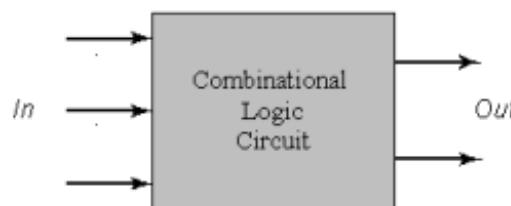
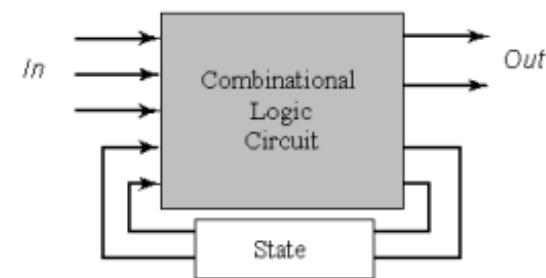


Combinational vs. Sequential Logic



Combinational

$$\text{Output} = f(\text{In})$$

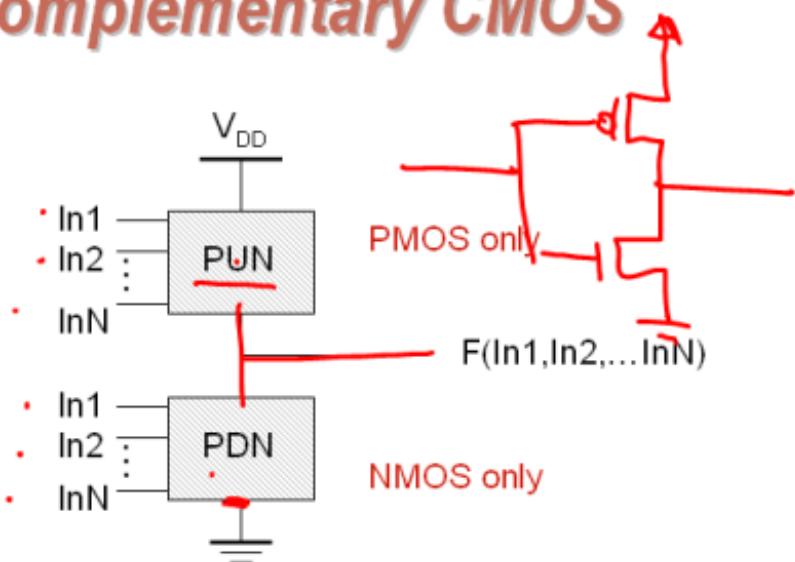


Sequential

$$\text{Output} = f(\text{In}, \text{Previous In})$$

Static Complementary CMOS

Pull Down Network



PUN and PDN are **dual** logic networks

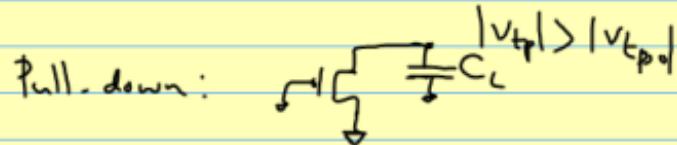
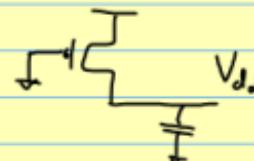
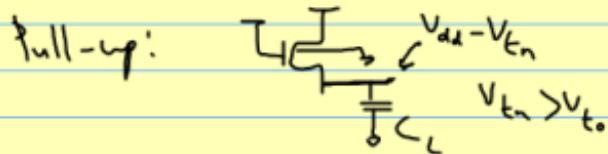
Combinational Logic

ch6

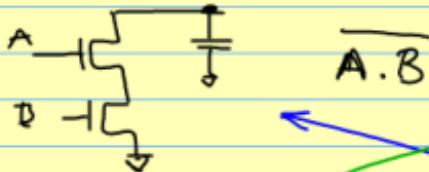
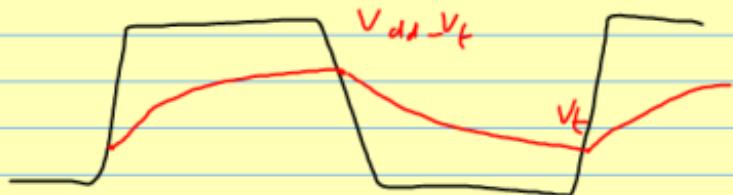
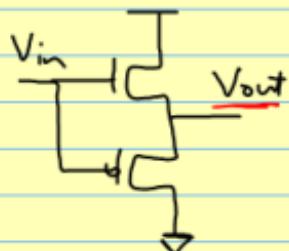
Static CMOS

- PUN and PDN EXCLUSIVE

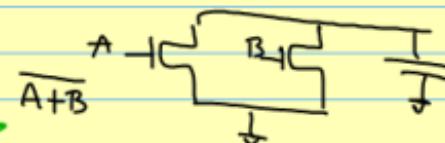
\Rightarrow out conn EITHER V_{dd} or GND



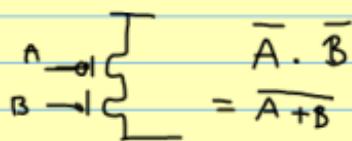
Logic Gates



$$\overline{A \cdot B}$$

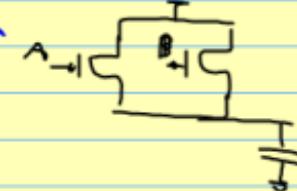


$$\overline{A+B}$$

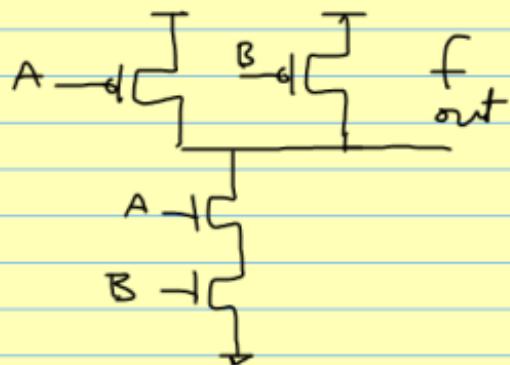


$$\overline{\overline{A} \cdot \overline{B}} = \overline{A+B}$$

$$\overline{\overline{A} + \overline{B}} = \overline{AB}$$



NAND Gate (Static, Comp(Mos))

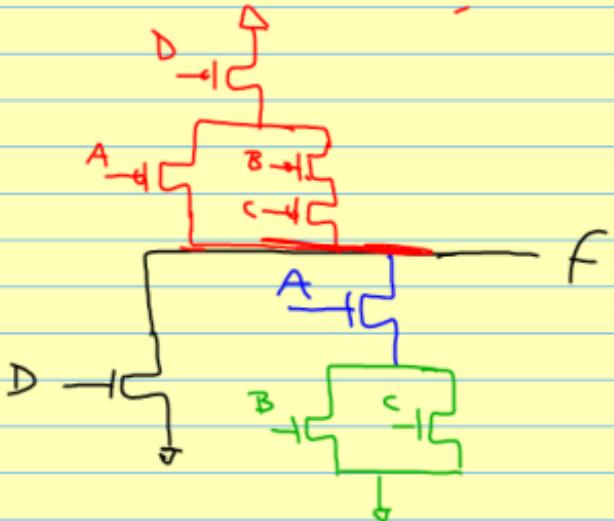


A	B	f
0	0	1
0	1	1
1	0	1
1	1	0

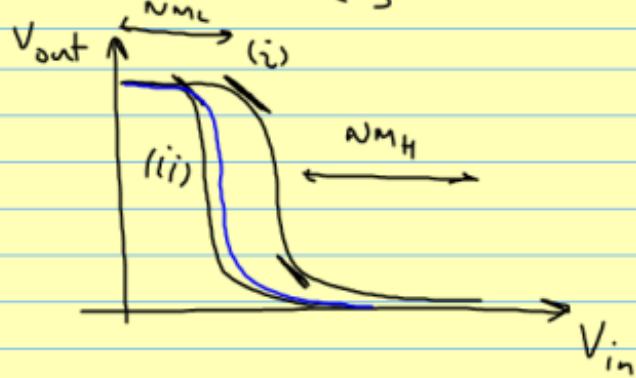
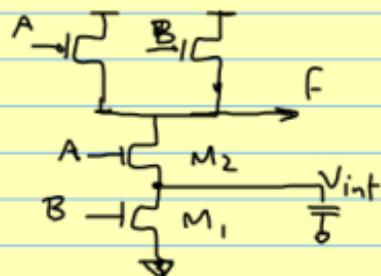
- Dual networks (series \leftrightarrow parallel)
- inverting logic
- AND logic? add inv to out
- N inp func $\longrightarrow 2^N$ tr

Complex CMOS func

$$F = \overline{D} + \underline{\underline{A \cdot (\overline{B} + C)}}$$



DC characteristics



(i) $A = B : 0 \rightarrow 1$

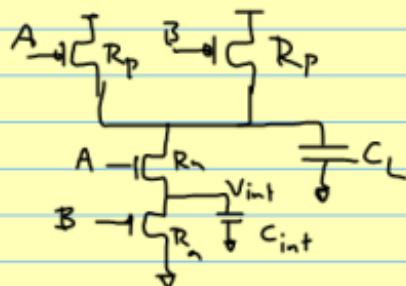
(ii) $A = 1, B : 0 \rightarrow 1$ (pull up weaker (i)).

(iii) $B = 1, A : 0 \rightarrow 1$ nmos not as strong as (ii)

$$V_t(M_1) = V_{t_0}$$

$$V_t(M_2) = V_{t_0} + \gamma \left(\sqrt{2\gamma_B + V_{int}} - \sqrt{2\gamma_B} \right)$$

NAND: Propagation Delay

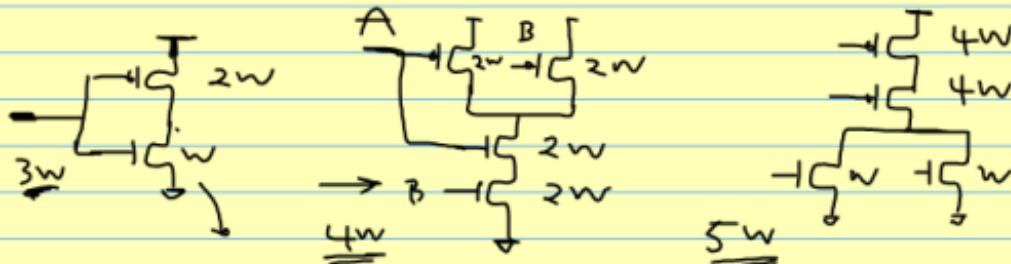


$$t_{PLH} = \begin{cases} A = B : 1 \rightarrow 0 \\ 0.69 \frac{R_p}{2} \cdot C_L \end{cases}$$

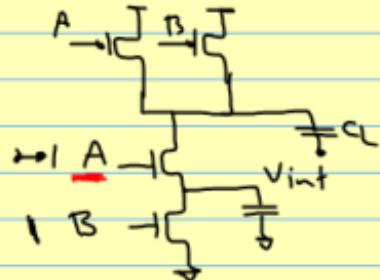
$B = 1, A : 1 \rightarrow 0 \quad (A = 1, B : 1 \rightarrow 0)$

$$0.69 R_p C_L$$

$$t_{PHL} = 0.69 \times 2 R_n C_L$$



Simulation NAND



t_{PLH}

- (i) $A=B: 1 \rightarrow 0$ fastest 35ps
- (ii) $A=1, B=1 \rightarrow 0$ slowest 76ps
- (iii) $B=1, A: 1 \rightarrow 0$ 57ps

t_{PHL}

- (i) $A=B: 0 \rightarrow 1$ slowest 69ps
- (ii) $A=1, B: 0 \rightarrow 1$ 62ps
- (iii) $B=1, A: 0 \rightarrow 1$ fastest 50ps